

isc N-Channel MOSFET Transistor

MTW32N20E

• FEATURES

- With TO-247 packaging
- With low gate drive requirements
- Low switching loss
- Low on-state resistance
- Easy to drive
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

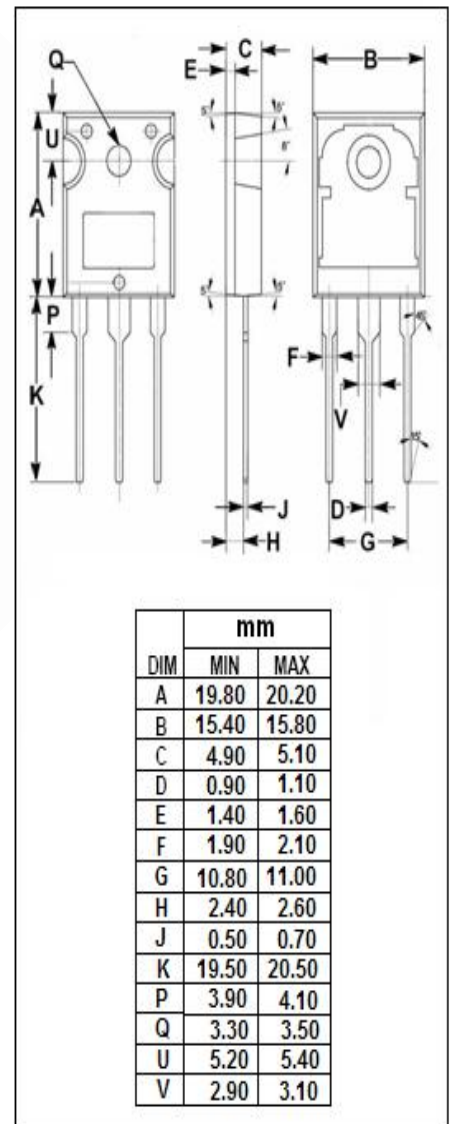
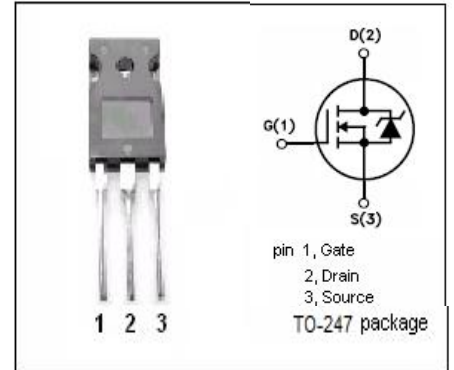
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	200	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous@T _c =25°C T _c =100°C	32 19	A
I _{DM}	Drain Current-Single Pulsed	128	A
P _D	Total Dissipation	180	W
T _j	Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	0.7	°C/W



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ELECTRICAL CHARACTERISTICS

 T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 0.25mA	200			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =±30V; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =16A		64	75	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±30V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 200V; V _{GS} = 0V; @T _c =25°C V _{DS} = 200V; V _{GS} = 0V; T _c =125°C			0.25 1.0	mA
V _{SDF}	Diode forward voltage	I _{SD} =32A, V _{GS} = 0V			2.0	V